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SZM-3166Z

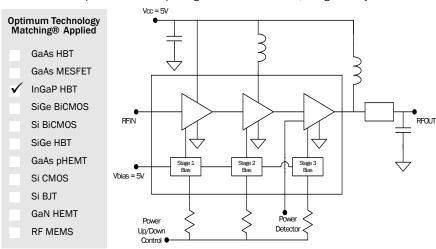
3.3 GHz to 3.6 GHz 2W POWER AMPLIFIER

Package: QFN, 6mmx6mm



Product Description

RFMD's SZM-3166Z is a high linearity class AB Heterojunction Bipolar Transistor (HBT) amplifier housed in a low-cost surface-mountable plastic Q-FlexN multi-chip module package. This HBT amplifier is made with InGaP on GaAs device technology and fabricated with MOCVD for an ideal combination of low cost and high reliability. This product is specifically designed for 802.16 customer premises equipment (CPE) terminals in the 3.3 GHz to 3.6 GHz bands. It can run from a 3V to 5.2V supply. The external output match and bias adjustability allows load line optimization for other applications covering 3.5 GHz to 3.8 GHz. It features an output power detector, on/off power control and high RF overdrive robustness. A 20dB step attenuator feature can be utilized by switching the second stage Power up/down control. This product features a RoHS compliant and Green package with matte tin finish, designated by the 'Z' suffix.



Features

- P_{1dB}=35dBm at 5.2V
- Three Stages of Gain: 35dB
- 802.11g 54 Mb/s Class AB Performance
- P_{OUT}=27 dBm at 2.5% EVM, V_{CC} 5.2V, 900 mA
- Active Bias with Adjustable Current
- On-Chip Output Power Detector
- Low Thermal Resistance
- Power Up/Down Control < 1µs</p>
- Attenuator Step 20dB at V_{PC2}=0V
- Class 1C ESD Rating

Applications

- 802.16 WiMAX Driver or Output Stage
- Fixed Wireless. WLL
- CPE Terminal Applications

| Parameter | Specification | | | Unit | Condition | |
|---------------------------------|---------------|------------|------|-------|--|--|
| Farameter | Min. | Тур. | Max. | Ullit | Condition | |
| Frequency of Operation | 3300 | | 3600 | MHz | | |
| Output Power at 1dB Compression | | 34.5 | | dBm | 3.5Ghz | |
| Gain | 32.0 | 35.0 | 38.0 | dBm | 3.5 Ghz, P _{OUT} =26 dBm | |
| % EVM | | 2.5 | | % | 3.5 GHz, P _{OUT} =27 dBm, 802.11g 54 Mb/s | |
| Third Order Suppression | | -42 | -37 | dBc | 3.5 GHz, P _{OUT} =23 dBm per tone | |
| Noise Figure | | 5.0 | | dB | 3.5GHz | |
| Worst Case Input Return Loss | 11.0 | 14.0 | | dB | 2.3 GHz to 3.5 GHz | |
| Worst Case Output Return Loss | 6.0 | 9.0 | | dB | 2.3 GHz to 3.5 GHz | |
| Supply voltage rang | | 5.2 | | V | | |
| Output Voltage Range | | 0.9 to 2.2 | | V | P _{OUT} =10dBm to 33dBm | |
| Quiescent Current | 720 | 800 | 880 | mA | V _{CC} =5.2V | |
| Power Up Control Current | | 5.0 | | mA | $V_{PC} = 5.2 \text{ V}, V_{VCP1} + V_{VPC2} + V_{VPC3} $ | |
| V _{CC} Leakage Current | | | 0.1 | μΑ | V _{CC} =5.2V, V _{PC} =0V | |
| Thermal Resistance | | 12.0 | | °C/W | junction - lead | |

Test Conditions: $Z_0 = 50\Omega$, $V_{CC} = 5.2V$, $I_0 = 800 \text{ mA}$, $T_{BP} = 30 ^{\circ}\text{C}$



Absolute Maximum Ratings

| Parameter | Rating | Unit |
|--|------------|------|
| VC3 Collector Bias Current (I _{VC3}) | 1500 | mA |
| VC2 Collector Bias Current (I _{VC2}) | 600 | mA |
| VC1 Collector Bias Current (I _{VC1}) | 300 | mA |
| **Device Voltage (V _D) | 9.0 | V |
| Power Dissipation (P _{DISS}) | 6 | W |
| Operating Temp Range (T _L) | -40 to +85 | °C |
| *Max RF output Power for 50Ω continuous long term operation | 30 | dBm |
| $\begin{array}{c} \text{Max RF Input Power (CW) for 50} \\ \text{output load} \end{array}$ | 29 | dBm |
| Max RF input Power for 10:1 VSWR output load | 5 | dBm |
| Max Storage Temp | +150 | °C |
| Operating Junction Temperature (T _J) | +150 | °C |
| ESD Rating - Human Body Model (HBM) | Class IC | |

Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

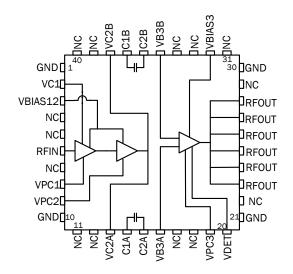
RoHS status based on EUDirective 2002/95/EC (at time of this document revision).

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Typical Performance 3.3 GHz to 3.6 GHz App Circuit (V_{CC}=5.2 V, I_{CO}=800 mA, *802.11g 54 Mb/s 64 QAM)

| Parameter | Unit | 3.3GHz | 3.4GHz | 3.5GHz | 3.6Ghz | 3.7GHz | 3.8GHz |
|--------------------------------------|------|--------|--------|--------|--------|--------|--------|
| Gain @ P _{OUT} =26dBm | dB | 35 | 35 | 35 | 35 | 33 | 31.5 |
| P_{1dB} | dBm | 34.0 | 34.5 | 35.0 | 34.5 | 34.0 | 33.0 |
| % EVM @ P _{OUT} =27dBm* | % | 2.7 | 2.5 | 2.5 | 2.6 | 3.1 | 4.0 |
| Current @ P _{OUT} 2.5% EVM* | mA | 930 | 930 | 920 | 893 | 910 | 885 |
| Input Return Loss | dB | 14.0 | 15.0 | 15.5 | 17.0 | 18.5 | 15.5 |
| Output Return Loss | dB | 9 | 10 | 10 | 9 | 8 | 7 |

Simplified Device Schematic

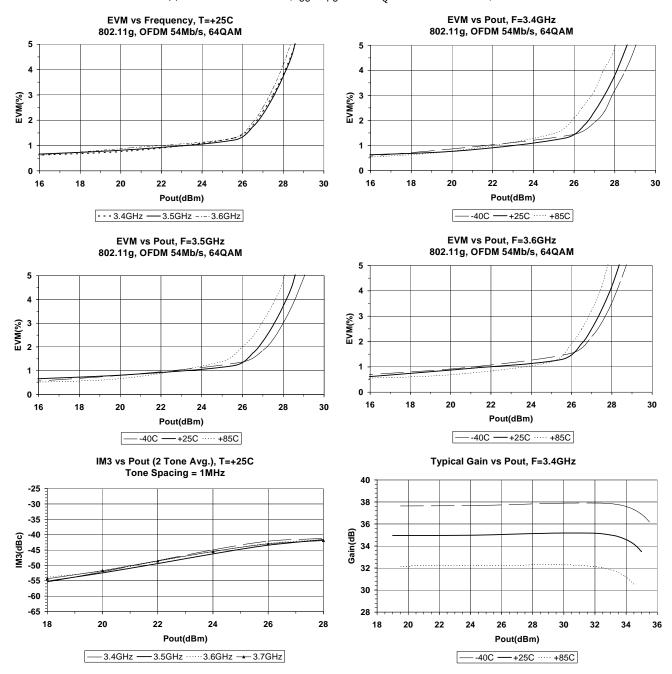


^{*}With specified application circuit
**No RF Drive
Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one. Bias Conditions should also satisfy the following expression:

 $I_DV_D < (T_J - T_L) / R_{TH}, i-1$



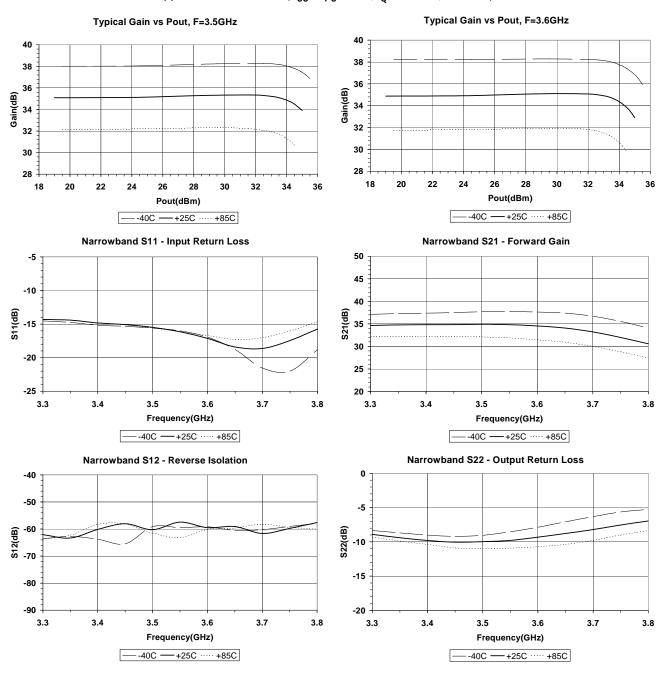
 $\textbf{Measured 3.3 GHz to 3.6 GHz Application Circuit Data (V_{CC}=V_{PC}=5.2 \text{V, I}_{Q}=800\,\text{mA, T}=25\,^{\circ}\text{C})}$



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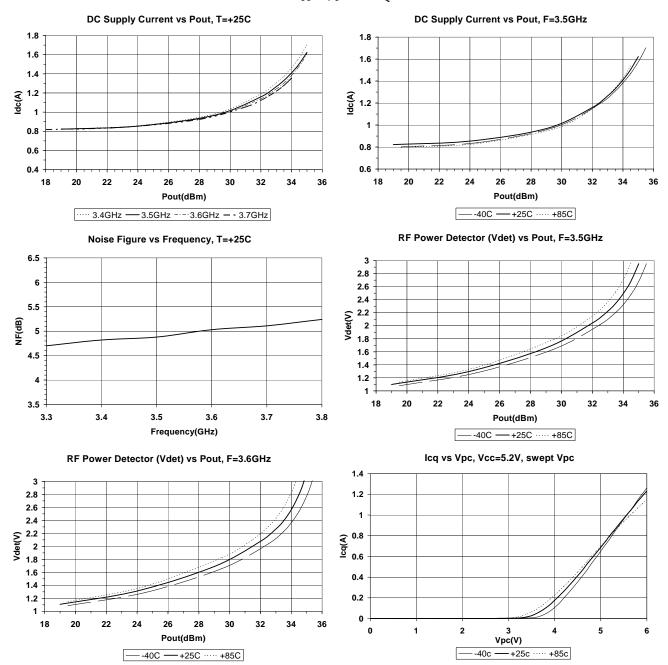


Measured 3.3 GHz to 3.6 GHz Application Circuit Data (V_{CC}=V_{PC}=5.2 V, I_Q=800 mA, T=25 $^{\circ}$ C)





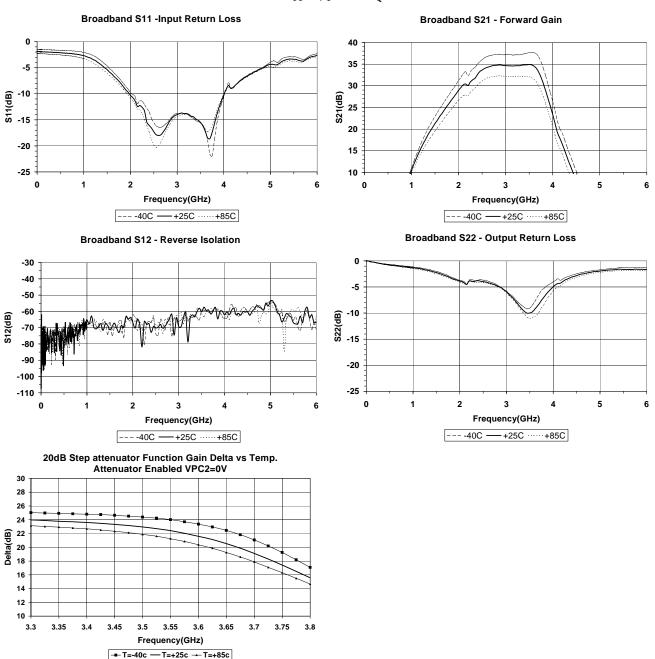
Measured 3.3 GHz to 3.6 GHz Application Circuit Data ($V_{CC} = V_{PC} = 5.2 \text{V}$, $I_Q = 800 \, \text{mA}$, $T = 25 \,^{\circ}\text{C}$)

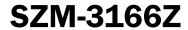


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Measured 3.3 GHz to 3.6 GHz Application Circuit Data ($V_{CC} = V_{PC} = 5.2 \text{V}$, $I_Q = 800 \, \text{mA}$, $T = 25 \,^{\circ}\text{C}$)





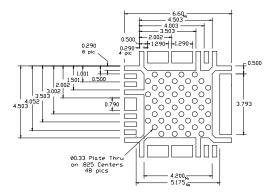


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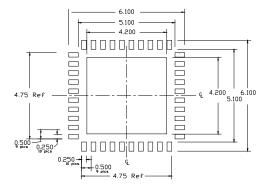
| Pin | Function | Description | | |
|--------------------|------------|---|--|--|
| 5, 7, 11, | NC | These are no connect (NC) pins and are not wired inside the package. It is recommended to connect them as show in the application circuit to achieve the stated performance. | | |
| 12, 17, | | | | |
| 18, 22, | | | | |
| 29, 31, 33, 34, | | | | |
| 39, 40 | | | | |
| 1, 10, | GND | These pins are internally grounded inside the package to the backside ground paddle. It is recommended to also | | |
| 21, 30 | GND | ground them external to the package to achieve the specified performance. | | |
| 2 | VC1 | This is the collector of the first stage. | | |
| 3 | VBIAS12 | This is the supply voltage for the active bias circuit of the 1st and 2nd stages. | | |
| 4 | NC | This pin is not connected inside the package, but it is recommended to connect it to GND to achieve the specified promance. | | |
| 6 | RF IN | This is the RF input pin. It is DC grounded inside the package. Do not apply DC voltage to this pin. | | |
| 8 | VPC1 | Power up/down control pin for the 1st stage. An external series resistor is required for proper setting of bias levels depending on control voltage. The voltage on this pin should never exceed the voltage on pin 3 by more than 0.5V unless the supply current from pin 3 is limited < 10 mA. | | |
| 9 | VPC2 | Power up/down control pin for the 2nd stage. Power down V _{PC2} <1V for step attenuator functionable. An external series resistor is required for proper setting of bias levels depending on control voltage. The voltage on this pin should never exceed the voltage on pin 3 by more than 0.5V unless the supply current from pin 3 is limited <10 mA. | | |
| 13, 38 | VC2A, VC2B | These two pins are connected internal to the package to the 2nd stage collector. To achieve specified performance, the layout of these pins should match the Recommended Land Pattern. | | |
| 14, 15, | C1A,C2A | These pins have capacitors across them internal to the package as shown in the below schematic. They are used as tuning and RF coupling elements between the 2nd and 3rd stage. | | |
| 36, 37 | C1B,C2B | tuning and M. Couping elements between the 2nd and 3rd stage. | | |
| 16, 35 | VB3A, VB3B | These are the connections to the base of the 3rd stage output device. To achieve specified performance, the layout of these pins should match the Recommended Land Pattern. | | |
| 19 | VPC3 | Power up/down control pin for the 3rd stage. An external series resistor is required for proper setting of bias levels depending on control voltage. The voltage on this pin should never exceed the voltage on pin 32 by more than 0.5 unless the supply current from pin 33 is limited < 10 mA. | | |
| 20 | VDET | This is the output port for the power detector. It samples the power at the input of the 3rd stage. | | |
| 23-28 | RF OUT | These are the RF output pins and DC connections to the 3rd stage collector. | | |
| 32 | VBIAS3 | This is the supply voltage for the active bias circuit of the 3rd stage. | | |



Recommended Metal Land Pattern

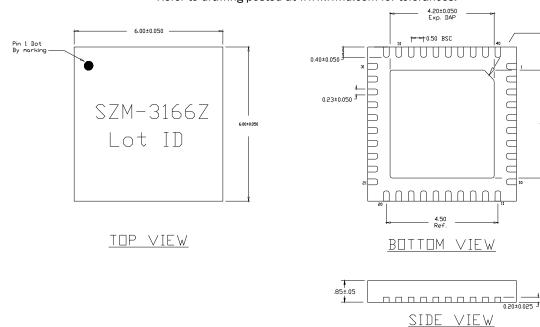


Recommended PCB Soldermask for Land Pattern



Package Drawing

Dimensions in inches (millimeters)
Refer to drawing posted at www.rfmd.com for tolerances.

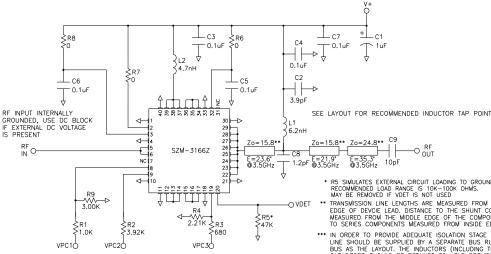


_PIN #1 IDENTIFICATION R0.200 TYP

4.20±0.050 Exp. DAP



3.3 GHz to 3.6 GHz Evaluation Board Schematic for $V_{CC} = V_{PC} = 5.2 V$

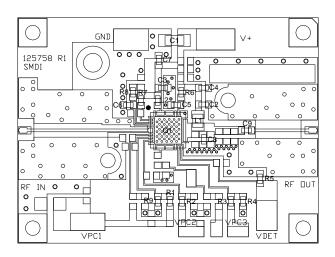


Note: For power up enable (Vpc) voltages < 5.2V, contact Applications Engineering for the appropriate R1, R9, R2, R3, and R4 values.

- R5 SIMULATES EXTERNAL CIRCUIT LOADING TO GROUND.
 RECOMMENDED LOAD RANGE IS 10K-100K OHMS.
 MAY BE REMOVED IF VDET IS NOT USED
 TRANSMISSION LINE LENGTHS ARE MEASURED FROM OUTSIDE
 EDGE OF DEVCIE LEAD. DISTANCE TO THE SHUNT COMPONENTS ARE
 MEASURED FROM THE MIDDLE EDGE OF THE COMPONENT; DISTANCE
 TO SERIES COMPONENTS MEASURED FROM INSIDE EDGE OF LAND PAD.
- IN ORDER TO PROVIDE ADEQUATE ISOLATION STAGE TO STAGE, EACH BIAS LINE SHOULD BE SUPPLIED BY A SEPARATE BUS RUNNING FROM THE MAIN POWER BUS AS THE LAYOUT. THE INDUCTORS (INCLUDING THE 0 OHM RESISTORS) AND CAPACITORS SHOULD BE RETAINED TO HELP PROVIDE ADEQUATE STAGE TO STAGE ISOLATION. ALTERNATE CONFIGURATIONS MAY IMPACT PERFORMANCE.



Evaluation Board Layout and Bill of Materials for $V_{CC} = V_{PC} = 5.2V$



Bill of Materials

| Desg | Description | Notes | | |
|----------------|------------------|---|--|--|
| Q1 | SZM-3166Z | 6mmx6mm QFN | | |
| R1 | 1.0ΚΩ, 0603 1% | 0402 may be used | | |
| R2 | 3.92ΚΩ, 0603 1% | 0402 may be used | | |
| R3 | 680Ω, 0603 1% | 0402 may be used | | |
| R4 | 2.21ΚΩ, 0603 1% | 0402 may be used | | |
| R5 | 47 ΚΩ, 0603 | 0402 may be used | | |
| R6, 7, 8 | 0Ω, 0603 | 0402 may be used | | |
| R9 | 3kW, 0603 1% | 0402 may be used | | |
| C1 | 1uF 16V MLCC CAP | Tantalum ok for EVM performance. Use MLCC type for best IM3 levels. | | |
| C2 | 3.9 pF CAP, 0603 | NPO, ROHM MCH185A3R9DK or equivalent | | |
| C3, 4, 5, 6, 7 | 0.1uF CAP, 0603 | X7R 0402 ok, ROHM MCH182CN104K or equivalent | | |
| C8 | 1.2 pF CAP, 0603 | NPO, low ESR, ATC 60052R4CW250 or equivalent | | |
| C9 | 10 pF CAP, 0603 | NPO, low EST, ATC 6005100JW250 or equivalent | | |
| L1 | 6.2 nH IND 0805 | Coilcraft 0805HQ - 6N2XJBB | | |
| L2 | 4.7 nH IND, 0603 | TOKO 0603 - LL1608FH4N7J | | |





Part Symbolization

The part will be symbolized with "SZM-3166Z" to designate it as an RoHS green compliant product. Marking designator will be on the top surface of the package.

SZM-3166Z



Ordering Information

| Ordering Code | Description |
|------------------|--|
| SZM3166ZSQ | Standard 25 piece bag |
| SZM3166ZSR | Standard 100 piece reel |
| SZM3166Z | Standard 1000 piece reel |
| SZM3166ZPCK-EVB1 | Evaluation Board 3.3GHz to 3.8GHz Tune and 5 loose sample pieces |